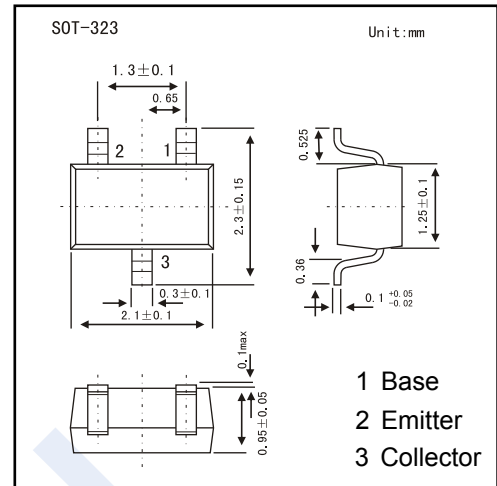


PNP Transistors

MMSTA92 (KMSTA92)

■ Features

- Small Surface Mount Package
- Ideal for Medium Power Amplification and Switching
- Complementary to MMSTA42



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-310	V
Collector - Emitter Voltage	V _{CE0}	-305	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-200	mA
Collector Current - Pulse	I _{CP}	-500	
Collector Power Dissipation	P _C	200	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E = 0	-310			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = -1 mA, I _B = 0	-305			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C = 0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -200 V, I _E = 0			-0.25	μA
Collector-emitter cut-off current	I _{CE0}	V _{CE} =-200V, I _B =0			-0.25	
		V _{CE} =-300V, I _B =0			-5	
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20 mA, I _B =-2mA			-0.2	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-20 mA, I _B =-2mA			-0.9	
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _C = -1mA	60			
	h _{FE(2)}	V _{CE} = -10V, I _C = -10mA	100		200	
	h _{FE(3)}	V _{CE} = -10V, I _C = -30mA	60			
Collector output capacitance	C _{ob}	V _{CB} =-20V, I _E =0, f=1MHz			6	pF
Transition frequency	f _T	V _{CE} = -20V, I _C = -10mA, f=30MHz	50			MHz

■ Marking

Marking	K3R

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■ Typical Characteristics

